

## XPT IGBT

$$V_{CES} = 1200V$$

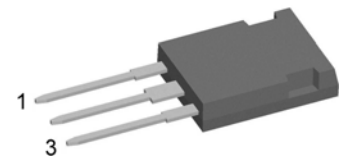
$$I_{C25} = 28A$$

$$V_{CE(sat)} = 1.8V$$

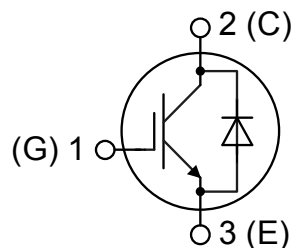
Copack

Part number

IXA17IF1200HJ



Backside: isolated

**Features / Advantages:**

- Easy paralleling due to the positive temperature coefficient of the on-state voltage
- Rugged XPT design (Xtreme light Punch Through) results in:
  - short circuit rated for 10  $\mu$ sec.
  - very low gate charge
  - low EMI
  - square RBSOA @ 3x  $I_c$
- Thin wafer technology combined with the XPT design results in a competitive low  $V_{CE(sat)}$
- SONIC™ diode
  - fast and soft reverse recovery
  - low operating forward voltage

**Applications:**

- AC motor drives
- Solar inverter
- Medical equipment
- Uninterruptible power supply
- Air-conditioning systems
- Welding equipment
- Switched-mode and resonant-mode power supplies
- Inductive heating, cookers
- Pumps, Fans

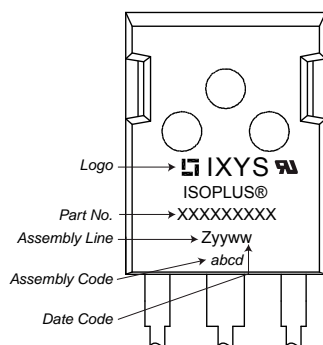
**Package: ISOPLUS247**

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Soldering pins for PCB mounting
- Backside: DCB ceramic
- Reduced weight
- Advanced power cycling

IGBT				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
$V_{CES}$	collector emitter voltage	$T_{VJ} = 25^{\circ}\text{C}$			1200	V	
$V_{GES}$	max. DC gate voltage				$\pm 20$	V	
$V_{GEM}$	max. transient gate emitter voltage				$\pm 30$	V	
$I_{C25}$	collector current	$T_C = 25^{\circ}\text{C}$			28	A	
$I_{C80}$		$T_C = 80^{\circ}\text{C}$			18	A	
$P_{tot}$	total power dissipation	$T_C = 25^{\circ}\text{C}$			100	W	
$V_{CE(sat)}$	collector emitter saturation voltage	$I_C = 15\text{A}; V_{GE} = 15\text{V}$		1.8	2.1	V	
				2.1		V	
$V_{GE(th)}$	gate emitter threshold voltage	$I_C = 0.6\text{mA}; V_{GE} = V_{CE}$	5.4	5.9	6.5	V	
$I_{CES}$	collector emitter leakage current	$V_{CE} = V_{CES}; V_{GE} = 0\text{V}$			0.1	mA	
				0.1		mA	
$I_{GES}$	gate emitter leakage current	$V_{GE} = \pm 20\text{V}$			500	nA	
$Q_{G(on)}$	total gate charge	$V_{CE} = 600\text{V}; V_{GE} = 15\text{V}; I_C = 15\text{A}$		47		nC	
$t_{d(on)}$	turn-on delay time	inductive load $V_{CE} = 600\text{V}; I_C = 15\text{A}$ $V_{GE} = \pm 15\text{V}; R_G = 56\Omega$	$T_{VJ} = 125^{\circ}\text{C}$	70		ns	
$t_r$	current rise time			40		ns	
$t_{d(off)}$	turn-off delay time			250		ns	
$t_f$	current fall time			100		ns	
$E_{on}$	turn-on energy per pulse			1.55		mJ	
$E_{off}$	turn-off energy per pulse			1.7		mJ	
<b>RBSOA</b>	reverse bias safe operating area	$V_{GE} = \pm 15\text{V}; R_G = 56\Omega$	$T_{VJ} = 125^{\circ}\text{C}$				
$I_{CM}$		$V_{CEmax} = 1200\text{V}$			45	A	
<b>SCSOA</b>	short circuit safe operating area	$V_{CEmax} = 900\text{V}$	$T_{VJ} = 125^{\circ}\text{C}$				
$t_{sc}$	short circuit duration	$V_{CE} = 900\text{V}; V_{GE} = \pm 15\text{V}$			10	$\mu\text{s}$	
$I_{sc}$	short circuit current	$R_G = 56\Omega; \text{non-repetitive}$			60	A	
$R_{thJC}$	thermal resistance junction to case				1.26	K/W	
$R_{thCH}$	thermal resistance case to heatsink			0.25		K/W	
<b>Diode</b>							
$V_{RRM}$	max. repetitive reverse voltage		$T_{VJ} = 25^{\circ}\text{C}$		1200	V	
$I_{F25}$	forward current		$T_C = 25^{\circ}\text{C}$		32	A	
$I_{F80}$			$T_C = 80^{\circ}\text{C}$		19	A	
$V_F$	forward voltage	$I_F = 20\text{A}$	$T_{VJ} = 25^{\circ}\text{C}$		2.20	V	
			$T_{VJ} = 125^{\circ}\text{C}$	1.95		V	
$I_R$	reverse current	$V_R = V_{RRM}$	$T_{VJ} = 25^{\circ}\text{C}$		*	mA	
	* not applicable, see Ices value above		$T_{VJ} = 125^{\circ}\text{C}$		*	mA	
$Q_{rr}$	reverse recovery charge	$V_R = 600\text{V}$ $-di_F/dt = -400\text{A}/\mu\text{s}$ $I_F = 20\text{A}; V_{GE} = 0\text{V}$	$T_{VJ} = 125^{\circ}\text{C}$	3		$\mu\text{C}$	
$I_{RM}$	max. reverse recovery current			20		A	
$t_{rr}$	reverse recovery time			350		ns	
$E_{rec}$	reverse recovery energy			0.7		mJ	
$R_{thJC}$	thermal resistance junction to case				1.5	K/W	
$R_{thCH}$	thermal resistance case to heatsink			0.25		K/W	

Package ISOPLUS247			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$I_{RMS}$	RMS current	per terminal			70	A
$T_{VJ}$	virtual junction temperature		-40		150	°C
$T_{op}$	operation temperature		-40		125	°C
$T_{stg}$	storage temperature		-40		150	°C
<b>Weight</b>				6		g
$F_C$	mounting force with clip		20		120	N
$d_{Spp/App}$	creepage distance on surface   striking distance through air	terminal to terminal	2.7			mm
$d_{Spbl/Apb}$		terminal to backside	4.1			mm
$V_{ISOL}$	isolation voltage	t = 1 second	3600			V
		t = 1 minute	3000			V

### Product Marking



### Part number

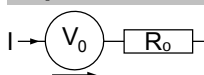
- I = IGBT
- X = XPT IGBT
- A = Gen 1 / std
- 17 = Current Rating [A]
- IF = Copack
- 1200 = Reverse Voltage [V]
- HJ = ISOPLUS247 (3)

Ordering	Part Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	IXA17IF1200HJ	IXA17IF1200HJ	Tube	30	507522

### Equivalent Circuits for Simulation

\* on die level

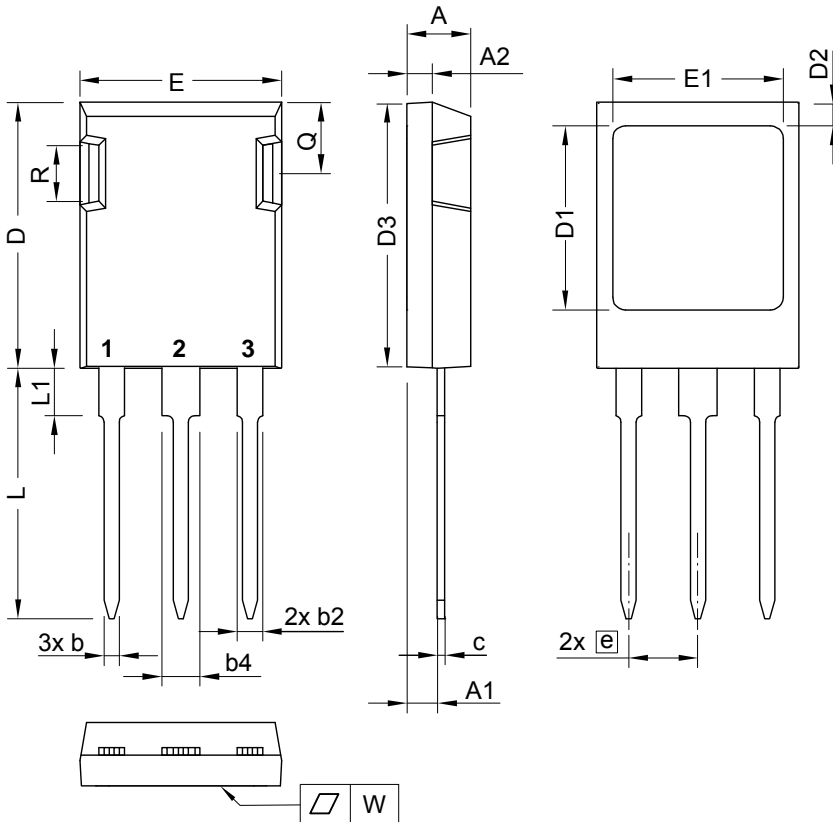
$T_{VJ} = 150\text{ °C}$



$V_{0\max}$  threshold voltage  
 $R_{0\max}$  slope resistance \*

	IGBT	Diode	
$V_{0\max}$	1.1	1.25	V
$R_{0\max}$	86	42.5	mΩ

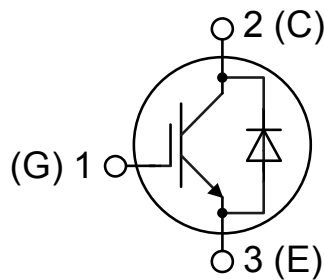
## Outlines ISOPLUS247



Dim.	Millimeter		Inches	
	min	max	min	max
A	4.83	5.21	0.190	0.205
A1	2.29	2.54	0.090	0.100
A2	1.91	2.16	0.075	0.085
b	1.14	1.40	0.045	0.055
b2	1.91	2.20	0.075	0.087
b4	2.92	3.24	0.115	0.128
c	0.61	0.83	0.024	0.033
D	20.80	21.34	0.819	0.840
D1	15.75	16.26	0.620	0.640
D2	1.65	2.15	0.065	0.085
D3	20.30	20.70	0.799	0.815
E	15.75	16.13	0.620	0.635
E1	13.21	13.72	0.520	0.540
e	5.45 BSC		0.215 BSC	
L	19.81	20.60	0.780	0.811
L1	3.81	4.38	0.150	0.172
Q	5.59	6.20	0.220	0.244
R	4.25	5.50	0.167	0.217
W	-	0.10	-	0.004

Die konvexe Form des Substrates ist typ. < 0.04 mm über der Kunststoffoberfläche der Bauteilunterseite  
 The convex bow of substrate is typ. < 0.04 mm over plastic surface level of device bottom side

Die Gehäuseabmessungen entsprechen dem Typ TO-247 AD gemäß JEDEC außer Schraubloch und  $L_{max}$ .  
 This drawing will meet all dimensions requirement of JEDEC outline TO-247 AD except screw hole and except  $L_{max}$ .



**IGBT**

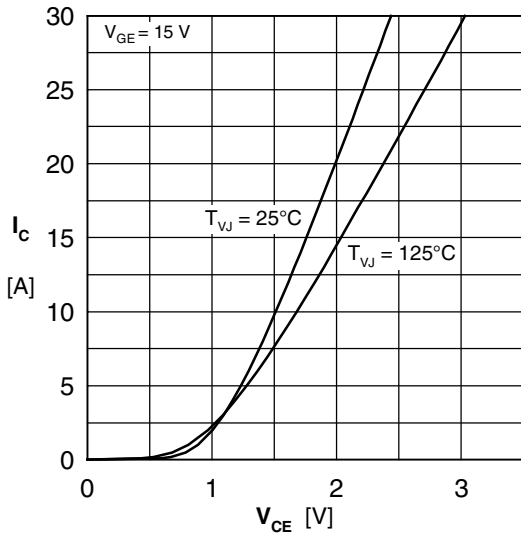


Fig. 1 Typ. output characteristics

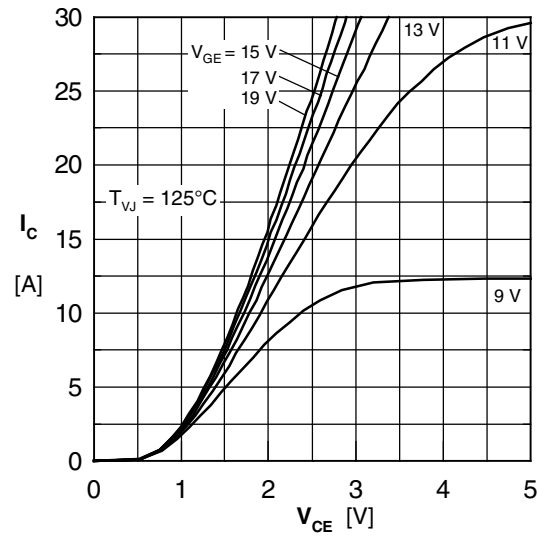


Fig. 2 Typ. output characteristics

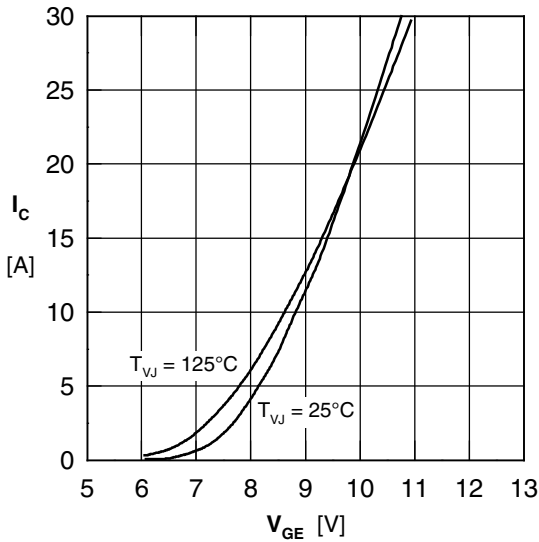


Fig. 3 Typ. transfer characteristics

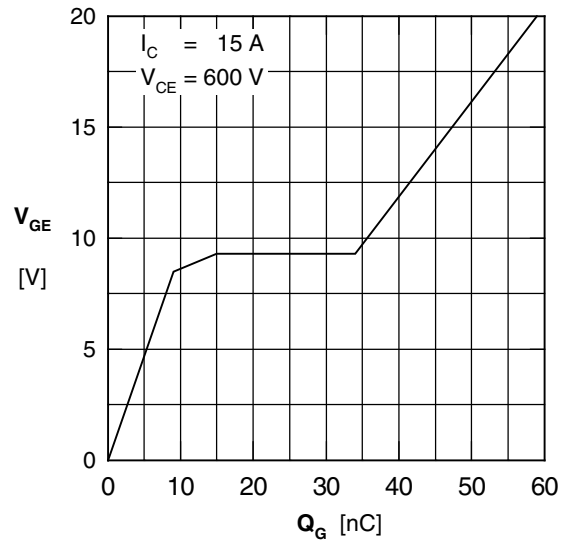


Fig. 4 Typ. turn-on gate charge

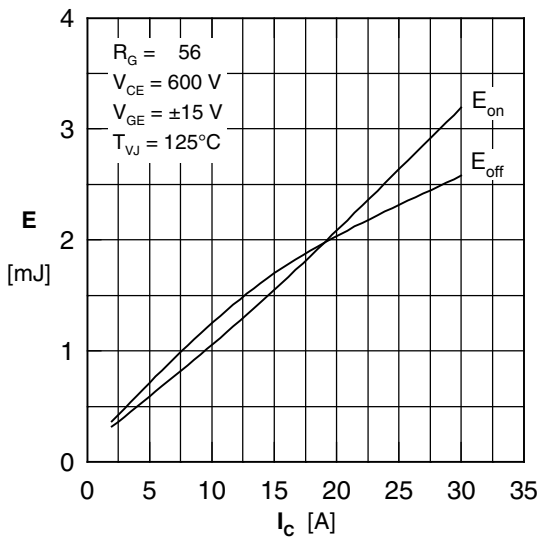


Fig. 5 Typ. switching energy vs. collector current

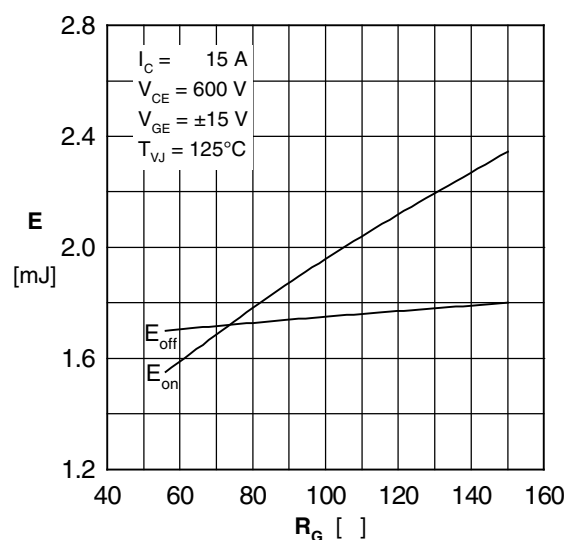


Fig. 6 Typ. switching energy vs. gate resistance